Performance characteristics:
- Frequency band: 6~18GHz
- NF: 1.4dB
- Gain: 21dB
- Input & Output RL: >10dB/>11dB
- Output P1dB: >7dBm
- Single power supply: +5V@73mA (or+3.5V@73mA)
- Dimension of Chip: 2.0mm×1.1mm×0.1mm

Short Description:
This product is GaAs MMIC Low Noise Amplifier Chip with Ultra-Wideband, frequency range covering 6~18GHz, the typical value of NF in the entire band is less than 1.5dB (Max 2.0dB). Can provide 21dB gain and the in-band flatness is less than 1dB. Using +3.5V or +5V single power supply.

Electrical parameters: (TA=25℃, VD=+5V, Id=73mA)

<table>
<thead>
<tr>
<th>Indicators</th>
<th>Min</th>
<th>Typical</th>
<th>Max</th>
<th>Unit</th>
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</thead>
<tbody>
<tr>
<td>Frequency Range</td>
<td>6~18</td>
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<td></td>
<td>GHz</td>
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<tr>
<td>NF</td>
<td>1.1</td>
<td>1.4</td>
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<tr>
<td>Gain</td>
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<td>22</td>
<td>dB</td>
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<tr>
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<td></td>
<td>dB</td>
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<tr>
<td>Output P1dB</td>
<td>7.5</td>
<td>10</td>
<td>13</td>
<td>dBm</td>
</tr>
</tbody>
</table>

Limitations parameters:
- Input power: +10dBm
- Control voltage: +5.5V
- Storage temperature: -65℃~150℃
- Operating temperature: -55℃~125℃

Outline Drawing (Unit: um)
1. Used in a clean environment, do not touch the surface of the chip during use;
2. For input and output, two (25um diameter gold wire) bonding wires are used, and the optimal length is about 300um
3. The input and output have DC blocking capacitors;
4. This product is a static sensitive device, please pay attention to anti-static during storage and use;
5. Store in dry, nitrogen environment.